**Listing of Claims**

Please amend the claims as follows. The following list of claims will replace all prior versions and listings of claims in the application.

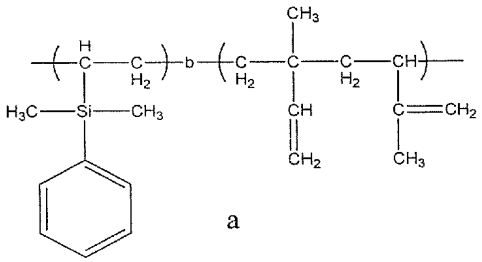
1-11. (Canceled)

12. (Previously Presented) A resist composition, comprising a silicon-containing resist polymer, wherein the silicon-containing resist polymer comprises poly(dimethylphenylvinylsilane-b-isoprene) having a molecular weight between about 17,800 and about 22,100.

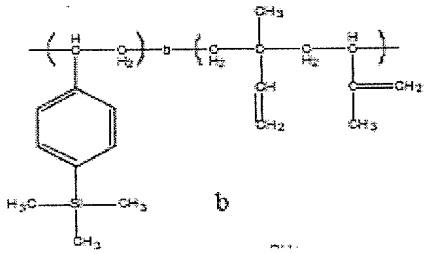
13. (Previously Presented) A resist composition, comprising a silicon-containing resist polymer, wherein the silicon-containing resist polymer comprises poly(trimethylsilylstyrene-b-isoprene) having a molecular weight between about 10,700 and about 28,700.

14-18. (Canceled)

19. (Previously Presented) A resist composition, comprising a silicon-containing resist polymer, wherein at least a portion of the silicon-containing resist polymer comprises a structure selected from the group consisting of:

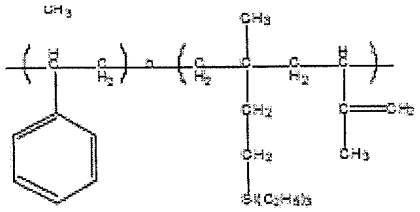


a



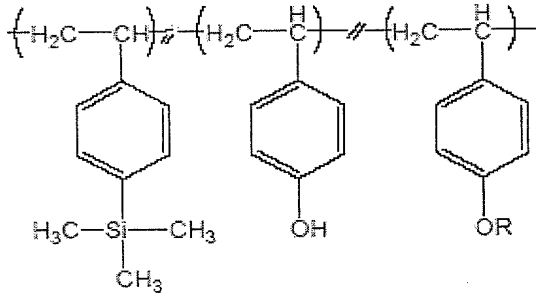
b

, and

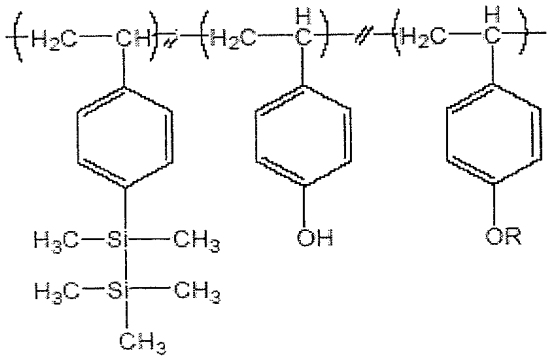


c

20. (Previously Presented) A resist composition, comprising a silicon-containing resist polymer, wherein at least a portion of the silicon-containing resist polymer comprises a structure selected from the group consisting of



and



,

wherein R represents a protecting group.

21. (Original) The resist composition of claim 20, wherein the protecting group R is selected from the group consisting of t-butyloxycarbonyl, trimethyl silane, and ethoxymethyl.

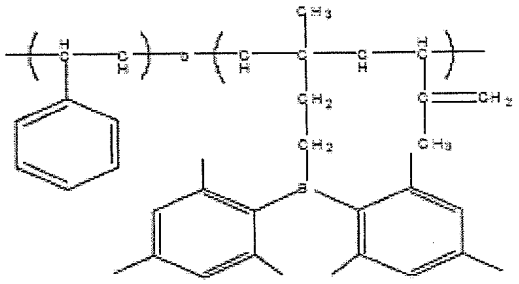
22-25. (Canceled)

26. (Currently Amended) A resist composition, comprising a boron-containing resist polymer,

wherein the boron-containing resist polymer comprises less than about 1 weight percent boron, and further comprises an element selected from the group consisting of ~~carborane,~~ carborane carboxylic acid, dimesitylborane and combinations thereof.

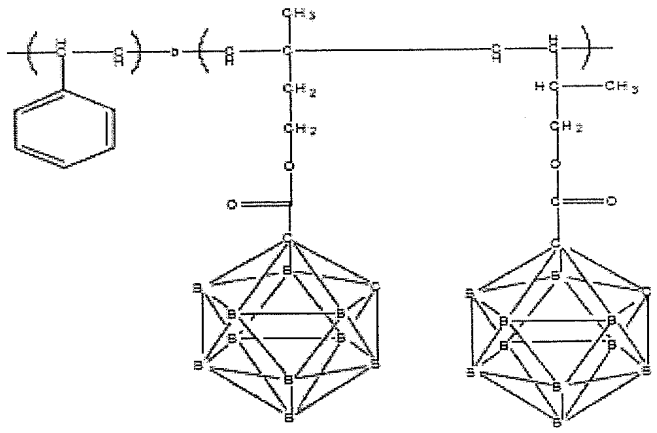
27-31. (Canceled)

32. (Previously Presented) A resist composition, comprising a boron-containing polymer, wherein the boron-containing polymer comprises a polymer having the structure:

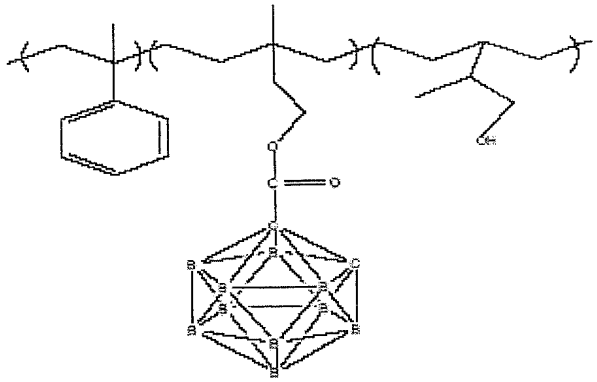


33. (Original) The resist composition of claim 32, wherein the resist composition comprises less than about 1 weight percent boron.

34. (Previously Presented) A resist composition, comprising a boron-containing polymer, wherein the boron-containing polymer comprises a polymer having the structure:



35. (Previously Presented) A resist composition, comprising a boron-containing polymer, wherein the boron-containing polymer comprises a boron-containing polymer having the structure:



36-45. (Canceled)

46-47. (Canceled)

48. (Currently Amended) A method for forming a boron-containing resist polymer, comprising performing a hydroboration or esterification reaction of a boron-containing group with a polymer, wherein the polymer comprises a polymer selected from the group consisting of ~~isoprene, styrene, vinyl compounds,~~ poly(styrene-b-isoprene)[[,]] and hydroxylated

poly(styrene-b-isoprene)~~, poly(styrene-b-hydroxystyrene), and poly(α-methylstyrene-b-hydroxystyrene)~~, to introduce dimesitylborane or a carborane into the polymer.

49-51. (Canceled)

52. (Previously Presented) A method for increasing the reactive ion etch resistance of a polymer, comprising incorporating boron atoms into the polymer, wherein incorporating boron atoms into the polymer further comprises performing hydroboration of the polymer, wherein the hydroboration agent comprises dimesitylborane.

53-66. (Canceled)